SGS-THOMSON MICROELECTRONICS

IRF240

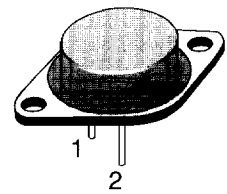
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
IRF240	200 V	0.18 Ω	18 A

- AVALANCHE RUGGEDNESS TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C

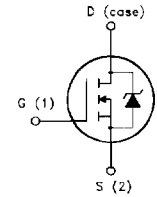
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- MOTOR CONTROL, AUDIO AMPLIFIERS
- INDUSTRIAL ACTUATORS
- DC-DC & DC-AC CONVERTERS FOR TELECOM, INDUSTRIAL AND CONSUMER ENVIRONMENT



TO-3

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	200	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	200	V
V_{GS}	Gate-source Voltage	± 20	V
I_D	Drain Current (cont.) at T_c = 25 °C	18	A
I_D	Drain Current (cont.) at T_c = 100 °C	11	A
I_{DM}(•)	Drain Current (pulsed)	72	A
P_{tot}	Total Dissipation at T_c = 25 °C	125	W
	Derating Factor	1	W/°C
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	1	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	30	°C/W
$R_{thc\text{-}s}$	Thermal Resistance Case-sink	Typ	0.1	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	18	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 25 V)	580	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	13	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (T_c = 100 °C, pulse width limited by T_j max, $\delta < 1\%$)	11	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	200			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 T_c = 125 °C			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V I_D = 10 A			0.18	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	18			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 10 A	6.7			S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0			2300 400 150	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING RESISTIVE LOAD

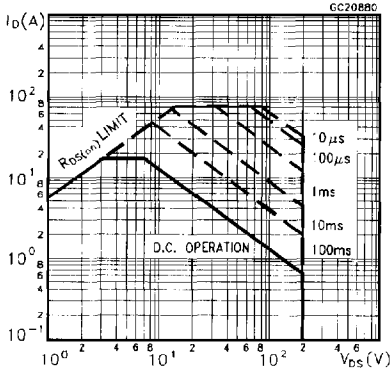
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	V_{DD} = 100 V I_D = 18 A		50	65	ns
t_r	Rise Time	R_G = 9.1 Ω V_{GS} = 10 V		90	120	ns
$t_{d(off)}$	Turn-off Delay Time	(see test circuit)		85	110	ns
t_f	Fall Time			60	80	ns
Q_g	Total Gate Charge	I_D = 18 A V_{GS} = 10 V V_{DD} = Max Rating x 0.8 (see test circuit)		65	85	nC

SOURCE DRAIN DIODE

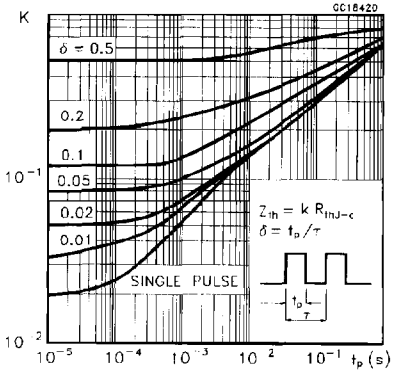
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				18	A
I_{SDM}(•)	Source-drain Current (pulsed)				72	A
V_{SD} (*)	Forward On Voltage	I_{SD} = 18 A V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 18 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		260		ns
Q_{rr}	Reverse Recovery Charge			2		µC

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
(•) Pulse width limited by safe operating area

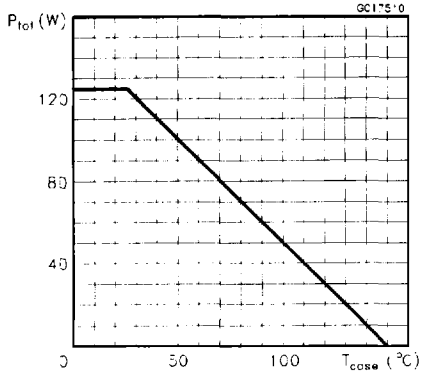
Safe Operating Area



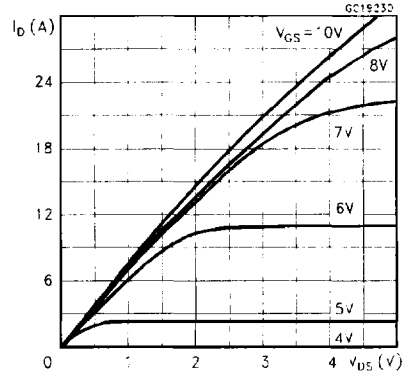
Thermal Impedance



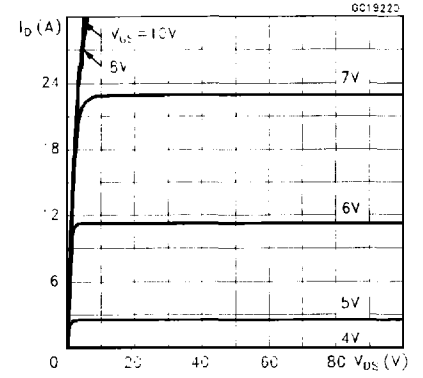
Derating Curve



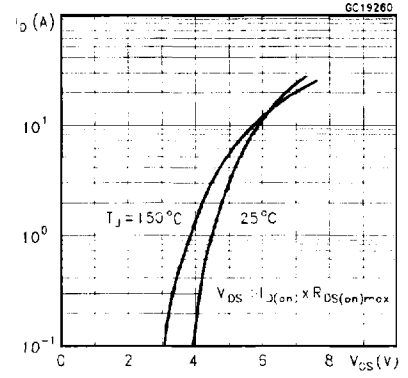
Output Characteristics



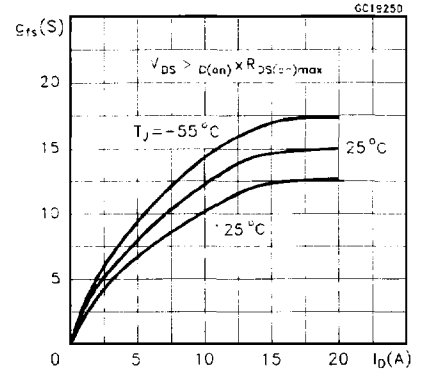
Output Characteristics



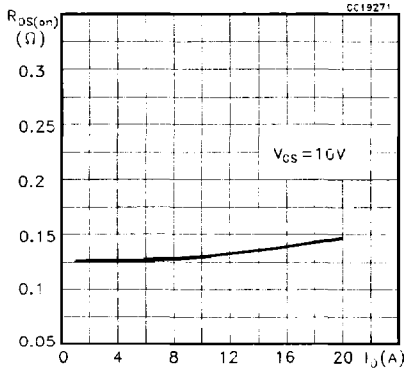
Transfer Characteristics



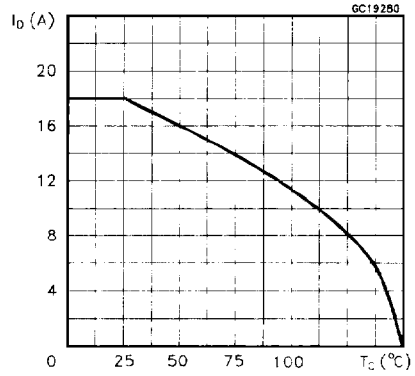
Transconductance



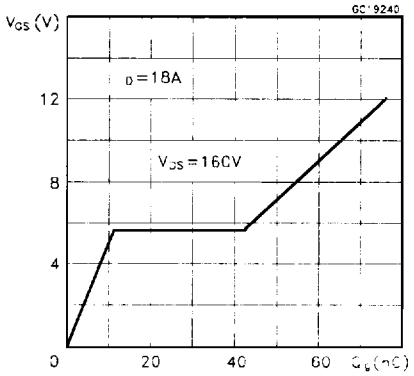
Static Drain-source On Resistance



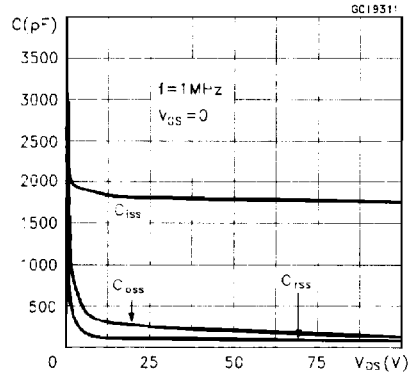
Maximum Drain Current vs Temperature



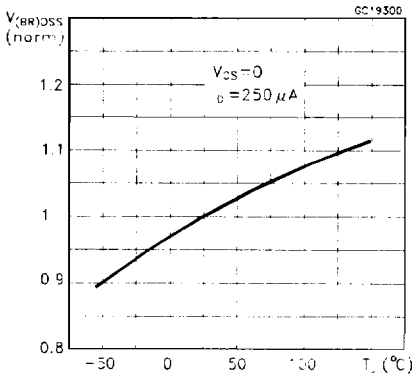
Gate Charge vs Gate-source Voltage



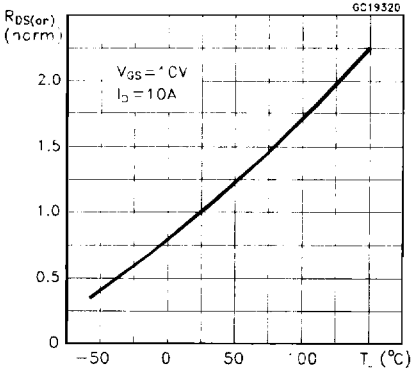
Capacitance Variations



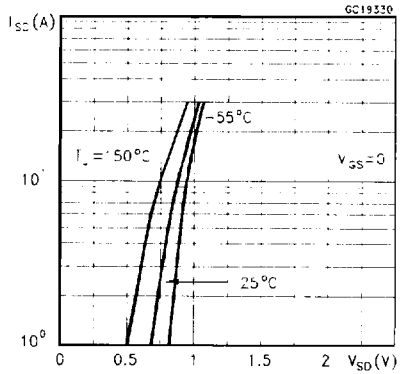
Normalized Breakdown Voltage vs Temperature



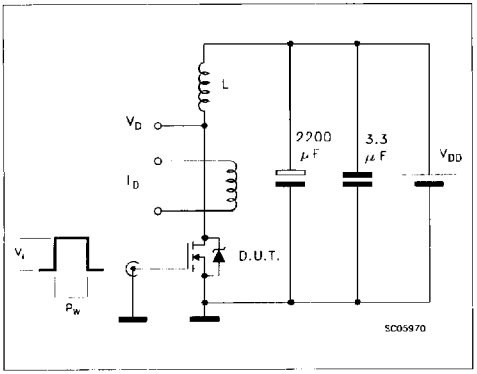
Normalized On Resistance vs Temperature



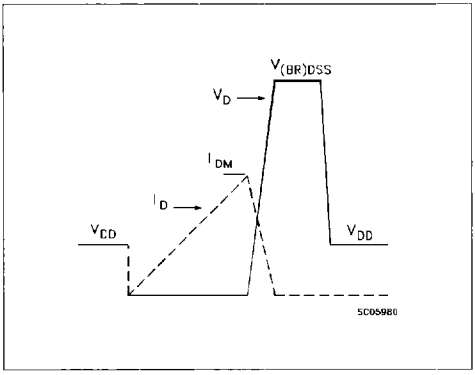
Source-drain Diode Forward Characteristics



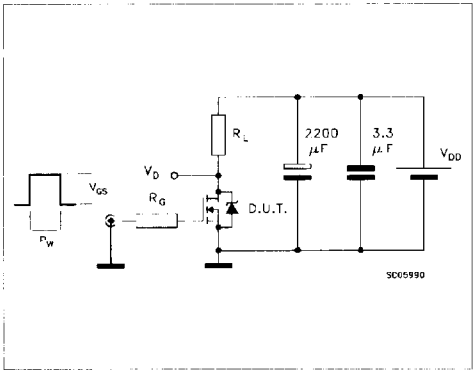
Unclamped Inductive Load Test Circuit



Unclamped Inductive Waveforms



Switching Time Test Circuit



Gate Charge Test Circuit